SN74LVC2G241 デュアル・バッファ/ドライバ、3-state 出力

1 特長

- テキサス・インスツルメンツの NanoFree™パッケージで供給
- 5V V_{CC}動作をサポート
- 5.5Vまでの入力電圧に対応
- 最大 t_{pd} 4.1ns (3.3V 時)
- 低消費電力、最大I_{CC} 10µA
- 3.3Vにおいて±24mAの出力駆動能力
- 標準V_{OLP}（出力グランド・バウンス）
  < 0.8V (V_{CC} = 3.3V、T_A = 25°C)
- 標準V_{OHV}（出力V_{OH}アンダーシュート）
  > 2V (V_{CC} = 3.3V、T_A = 25°C)
- I_{off} により活線挿抜、部分的パワーダウン・モード、バック・ドライブ保護をサポート
- 最高 5.5V の入力を V_{CC} レベルに変換する降圧トランスレータとして使用可能
- JESD 78, Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22を超えるESD保護
  - 2000V、人体モデル(A114-A)
  - 200V、マシン・モデル(A115-A)
  - 1000V、荷電デバイス・モデル(C101)

2 アプリケーション

- AVレシーバ
- Blu-ray プレーヤおよびホーム・シアター
- DVD レコーダおよびプレーヤ
- デスクトップ PC またはノート PC
- デジタル・ラジオまたはインターネット・ラジオ・プレーヤ
- デジタル・ビデオ・カメラ (DVC)
- 組み込み用 PC
- GPS：パーソナル・ナビゲーション・デバイス
- モバイル・インターネット・デバイス
- ネットワーク・プロジェクタのフロントエンド
- 携帯用メディア・プレーヤ
- プロ用オーディオ・ミキサー

3 概要

このデュアル・バッファおよびライン・ドライバは、1.65V～5.5V の V_{CC} で動作するよう設計されています。

SN74LVC2G241 デバイスは、3-state メモリ・アドレス・ドライバ、クロック・ドライバ、バス用レシーバ/トランスミッタの性能と密度の両方を向上することに特化して設計されています。

NanoFree パッケージ技術は IC パッケージの概念における主要なブレークスルーであり、ダイをパッケージとして使用します。

SN74LVC2G241 デバイスは、独立した出力イネーブル ($1\overline{OE}$、2OE) 入力を備えた 2 つの 1ビット・ライン・ドライバで構成されています。$1\overline{OE}$ が LOW、2OE が HIGH の場合、デバイスは A 入力からのデータを Y 出力に渡します。$1\overline{OE}$ が HIGH、2OE が LOW の場合、出力は高インピーダンス状態になります。

電源オンまたは電源オフ時に高インピーダンス状態になるように、$\overline{OE}$ をプルダウン抵抗経由で V_{CC} に接続し、OE をプルダウン抵抗経由で GND に接続する必要があります。この抵抗の最小値は、ドライバの電流シンクまたは電流ソース能力によって決まります。

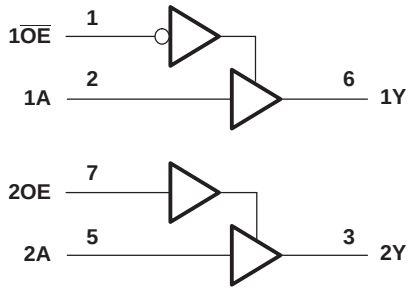
このデバイスは、I_{off}を使用する部分的パワーダウン・アプリケーション用に完全に動作が規定されています。I_{off}回路が出力をディセーブルにするため、電源切断時にデバイスに電流が逆流して損傷に至ることを回避できます。

製品情報(1)

型番	パッケージ	本体サイズ(公称)
SN74LVC2G241DCT	SM8 (8)	2.95mm×2.80mm
SN74LVC2G241DCU	VSOOP (8)	2.30mm×2.00mm
SN74LVC2G241YZP	DSBGA (8)	1.91mm×0.91mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

ロジック図 (正論理)



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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision O (December 2015) から **Revision P** に変更 **Page**

- Changed Electrical Characteristics table format ... 5
- Changed Switching Characteristics tables format. ... 6

Revision N (November 2013) から **Revision O** に変更 **Page**

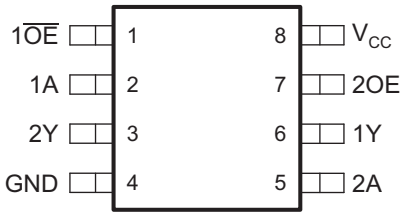
- 「*アプリケーション*」セクション、「*製品情報*」表、「*ESD定格*」表、「*熱に関する情報*」表、「*代表的特性*」セクション、「*機能説明*」セクション、「*デバイスの機能モード*」セクション、「*アプリケーションと実装*」セクション、「*電源に関する推奨事項*」セクション、「*レイアウト*」セクション、「*デバイスおよびドキュメントのサポート*」セクション、「*メカニカル、パッケージ、および注文情報*」セクションを追加 ... 1

Revision M (February 2007) から **Revision N** に変更 **Page**

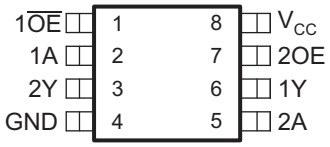
- ドキュメントを新しい TI データシートのフォーマットに更新 ... 1
- 「注文情報」表を削除 ... 1
- 「特長」を更新 ... 1
- Updated operating temperature range. ... 4

5 Pin Configuration and Functions

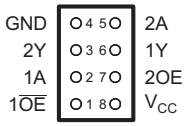
DCT Package
8-Pin SM8
Top View



DCU Package
8-Pin VSSOP
Top View



YZP Package
8-Pin DSBGA
Bottom View



Pin Functions[1][2]

PIN		I/O	DESCRIPTION
NAME	NO.		
1A	2	I	Input
$\overline{1OE}$	1	I	Output enable (Active low)
1Y	6	O	Output
2A	5	I	Input
2Y	3	O	Output
2OE	7	I	Output enable (Active high)
GND	4	—	Ground
V_{CC}	8	—	Power pin

(1) N.C. – No internal connection
(2) See for dimensions

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Voltage applied to any output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Voltage applied to any output in the high or low state(2)(3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_J	Maximum junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 3 V to 3.6 V	2		
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 3 V to 3.6 V		0.8	
		V_{CC} = 4.5 V to 5.5 V		0.3 × V_{CC}	
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3-state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 3 V		–16	
				–24	
		V_{CC} = 4.5 V		–32	

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report *Implications of Slow or Floating CMOS Inputs*, SCBA004.

Recommended Operating Conditions(1) (continued)

			MIN	MAX	UNIT
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 3 V		16	
				24	
		V_{CC} = 4.5 V		32	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V_{CC} = 3.3 V ± 0.3 V		10	
		V_{CC} = 5 V ± 0.5 V		5	
T_A	Operating free-air temperature		–40	85	°C

6.4 Thermal Information

THERMAL METRIC(1)		SN74LVC2G241			UNIT
		DCT (SM8)	DCU (VSSOP)	YZP (DSBGA)	
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	220	227	102	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range, T_A = –40ºC to 125°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	–40°C to 85°C			–40°C to 125°C (Recommended)			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}		I_{OH} = –100 µA	1.65 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
		I_{OH} = –4 mA	1.65 V	1.2			1.2			
		I_{OH} = –8 mA	2.3 V	1.9			1.9			
		I_{OH} = –16 mA	3 V	2.4			2.4			
		I_{OH} = –24 mA		2.3			2.3			
		I_{OH} = –32 mA	4.5 V	3.8			3.8			
V_{OL}		I_{OL} = 100 µA	1.65 V to 5.5 V			0.1			0.1	V
		I_{OL} = 4 mA	1.65 V			0.45			0.45	
		I_{OL} = 8 mA	2.3 V			0.3			0.3	
		I_{OL} = 16 mA	3 V			0.4			0.4	
		I_{OL} = 24 mA				0.55			0.55	
		I_{OL} = 32 mA	4.5 V			0.55			0.75	
I_I	A or $\overline{OE}$ inputs	V_I = 5.5 V or GND	0 to 5.5 V			±5			±5	µA
I_{off}		V_I or V_O = 5.5 V	0			±10			±10	µA
I_{OZ}		V_O = 0 to 5.5 V	3.6 V			10			10	µA
I_{CC}		V_I = 5.5 V or GND, I_O = 0	1.65 V to 5.5 V			10			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V			500			500	µA
C_i	Data Inputs	V_I = V_{CC} or GND	3.3 V		3.5					pF
	Control Inputs				4					
C_o		V_O = V_{CC} or GND	3.3 V		6.5					pF

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 85°C								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	3.3	9.1	1.5	5.5	1.4	4.3	1.0	4.0	ns
t_{en}	$\overline{OE}$	Y	4.0	9.9	1.3	6.6	1.2	4.7	1.1	5.0	ns
t_{dis}	$\overline{OE}$	Y	1.5	11.6	1.0	5.7	1.4	4.6	0.5	4.2	ns

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 125°C (Recommended)								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	3.3	10.1	1.5	5.6	1.4	5.3	1.0	4.2	ns
t_{en}	$\overline{OE}$	Y	4.0	10.9	1.3	6.6	1.2	5.7	1.2	4.3	ns
t_{dis}	$\overline{OE}$	Y	1.5	12.6	1.0	6.6	1.4	5.6	1.0	3.9	ns

6.7 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd} Power dissipation capacitance per buffer/driver	Outputs enabled	f = 10 MHz	V_{CC} = 1.8 V	19	pF
			V_{CC} = 2.5 V	19	
			V_{CC} = 3.3 V	20	
			V_{CC} = 5 V	22	
	Outputs disabled		V_{CC} = 1.8 V	2	pF
			V_{CC} = 2.5 V	2	
			V_{CC} = 3.3 V	2	
			V_{CC} = 5 V	3	

6.8 Typical Characteristic

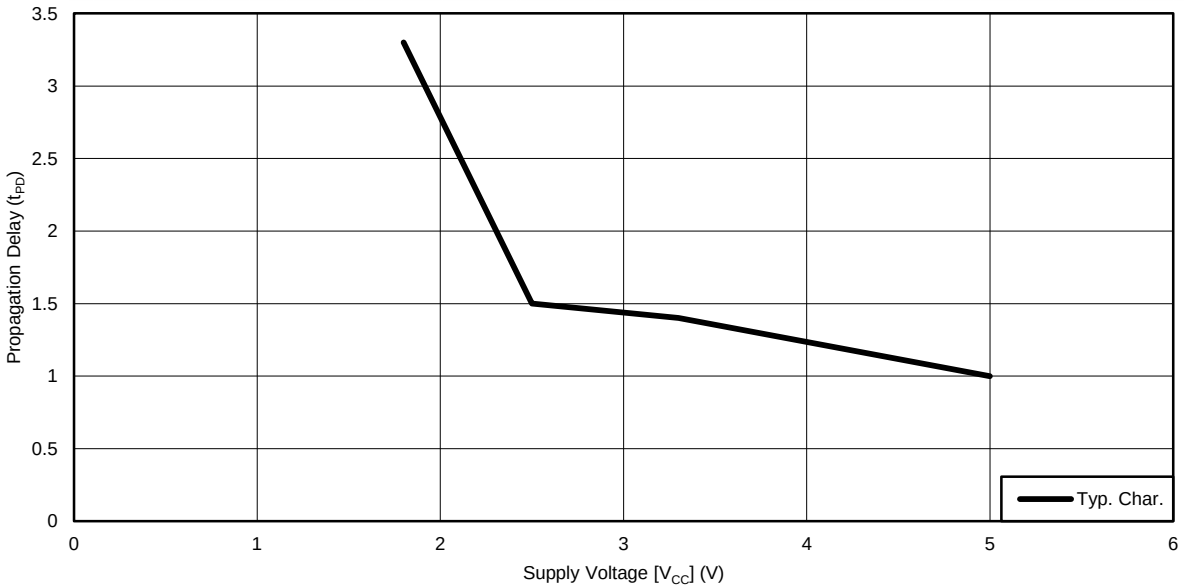
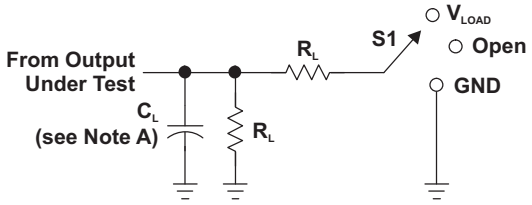


Figure 1. tpd vs Vcc Over Full Temperature Range

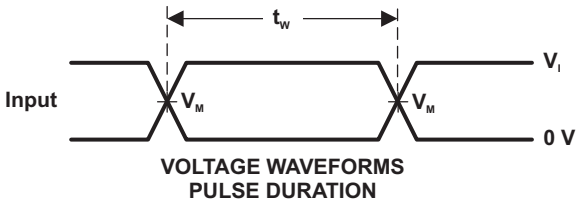
7 Parameter Measurement Information



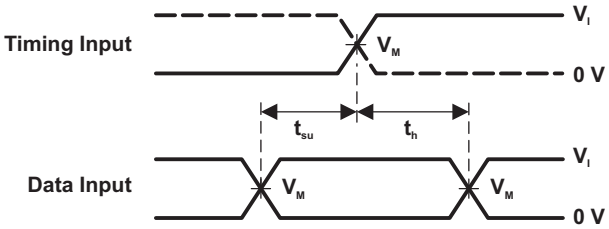
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

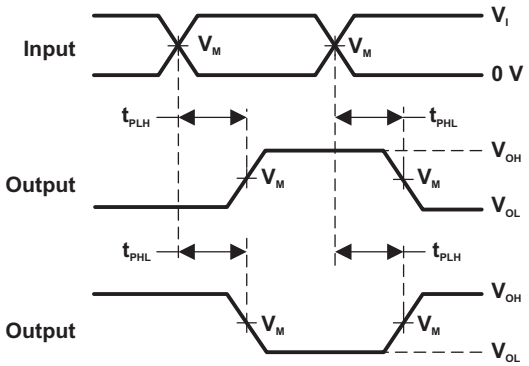
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	50 pF	500 Ω	0.3 V



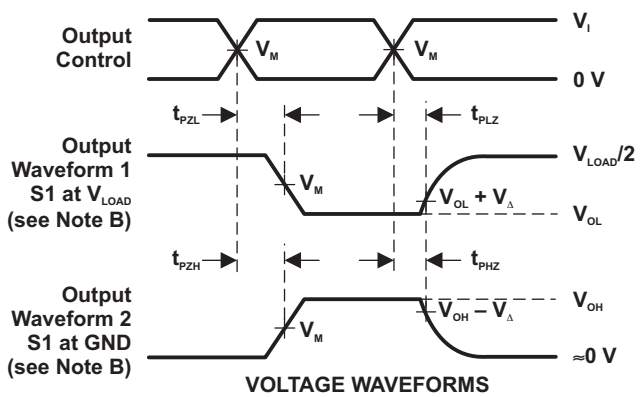
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LVC2G241 device is designed specifically to improve both the performance and density of 3-state memory-address drivers, clock drivers, and bus-oriented receivers and transmitters. The SN74LVC2G241 device is organized as two 1-bit line drivers with separate output-enable ($1\overline{OE}$, 2OE) inputs. When $1\overline{OE}$ is low and 2OE is high, the device passes data from the A inputs to the Y outputs. When $1\overline{OE}$ is high and 2OE is low, the outputs are in the high-impedance state.

The SN74LVC2G241 is also an effective redriver, with a maximum output current drive of 32 mA.

8.2 Functional Block Diagram

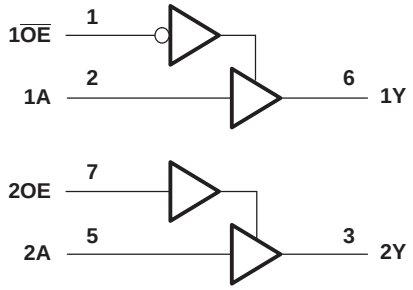


Figure 3. Logic Diagram (Positive Logic)

8.3 Feature Description

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor, and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.4 Device Functional Modes

Table 1 and Table 2 list the functional modes of the SN74LVC2G241.

Table 1. Gate 1 Functional Table

INPUTS		OUTPUT 1Y
$1\overline{OE}$	1A	
L	H	H
L	L	L
H	X	Z

Table 2. Gate 2 Functional Table

INPUTS		OUTPUT 2Y
2OE	2A	
H	H	H
H	L	L
L	X	Z

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Typical Application shows a simple application where a physical push button is connected to the SN74LVC2G241. The push button is in a physical location far enough away from the processor that the input signal is weak and needs to be redriven. The SN74LVC2G241 acts as a redriver, providing a strong input signal to the processor with as little as 1 ns of propagation delay.

9.2 Typical Application

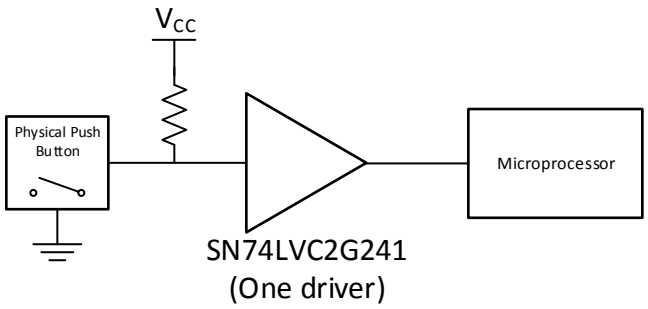


Figure 4. SN74LVC2G241 Application

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive also creates fast edges into light loads, so routing and load conditions must be considered to prevent ringing.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions
   - Rise time and fall time specs. See ($\Delta t/\Delta V$) in *Recommended Operating Conditions*.
   - Specified high and low levels. See (V_{IH} and V_{IL}) in *Recommended Operating Conditions*.
   - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in *Recommended Operating Conditions* at any valid V_{CC}.
2. Recommend Output Conditions
   - Load currents must not exceed (I_O max) per output and must not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in *Absolute Maximum Ratings*.
   - Outputs must not be pulled above V_{CC} during normal operation or 5.5 V in high-z state.

Typical Application (continued)

9.2.3 Application Curve

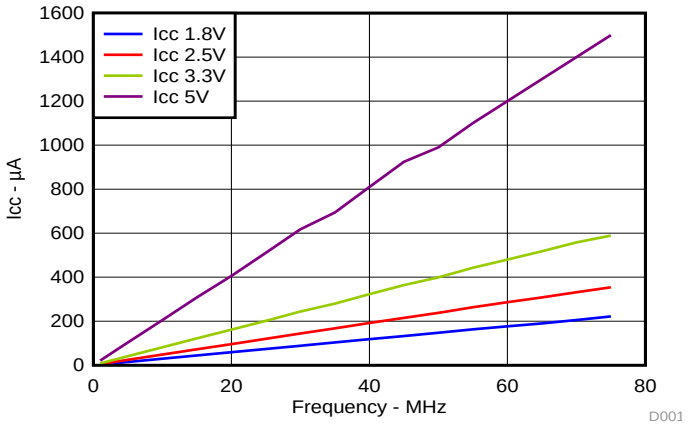


Figure 5. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in *Recommended Operating Conditions*.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-µF capacitor is recommended and if there are multiple V_{CC} pins then a 0.01-µF or 0.022-µF capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs must not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever make more sense or is more convenient.

11.2 Layout Example

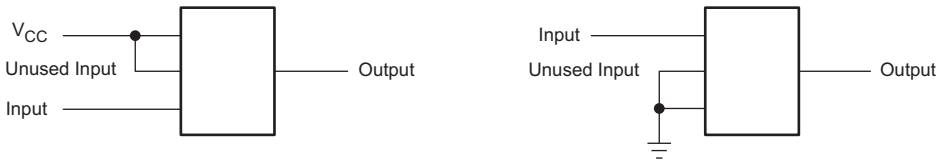


Figure 6. Layout Diagram

12 デバイスおよびドキュメントのサポート

12.1 ドキュメントのサポート

12.1.1 関連資料

関連資料については、以下を参照してください。

『低速またはフローティングCMOS入力の影響』、SCBA004

12.2 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™オンライン・コミュニティ ***TIのE2E（Engineer-to-Engineer）コミュニティ。***エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイディアを検討して、問題解決に役立てることができます。

設計サポート ***TIの設計サポート*** 役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

12.3 商標

NanoFree, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.4 静電気放電に関する注意事項

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12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。これらの情報は、指定のデバイスに対して提供されている最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。このデータシートのブラウザ対応版については、左側にあるナビゲーションを参照してください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC2G241DCTRE4	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
74LVC2G241DCTRG4	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
74LVC2G241DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41R	Samples
SN74LVC2G241DCTR	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(2WP5, C41) Z	Samples
SN74LVC2G241DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(C41J, C41Q, C41R)	Samples
SN74LVC2G241DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(C41J, C41Q, C41R)	Samples
SN74LVC2G241YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	(C2, C27)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

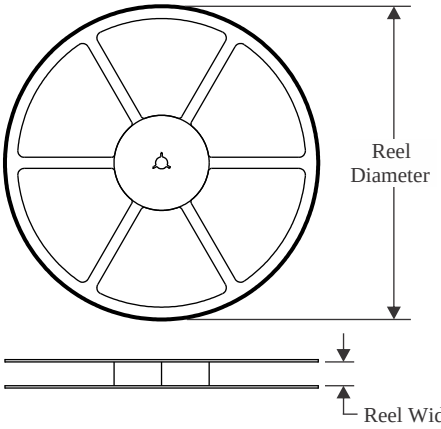
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

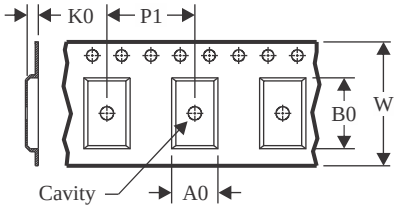
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

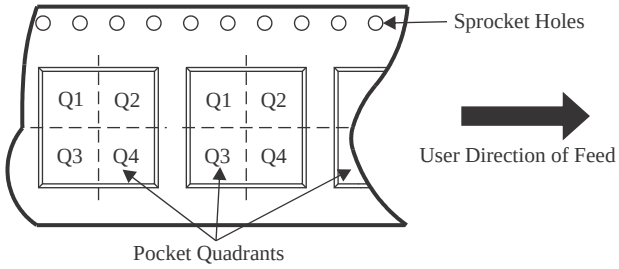


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

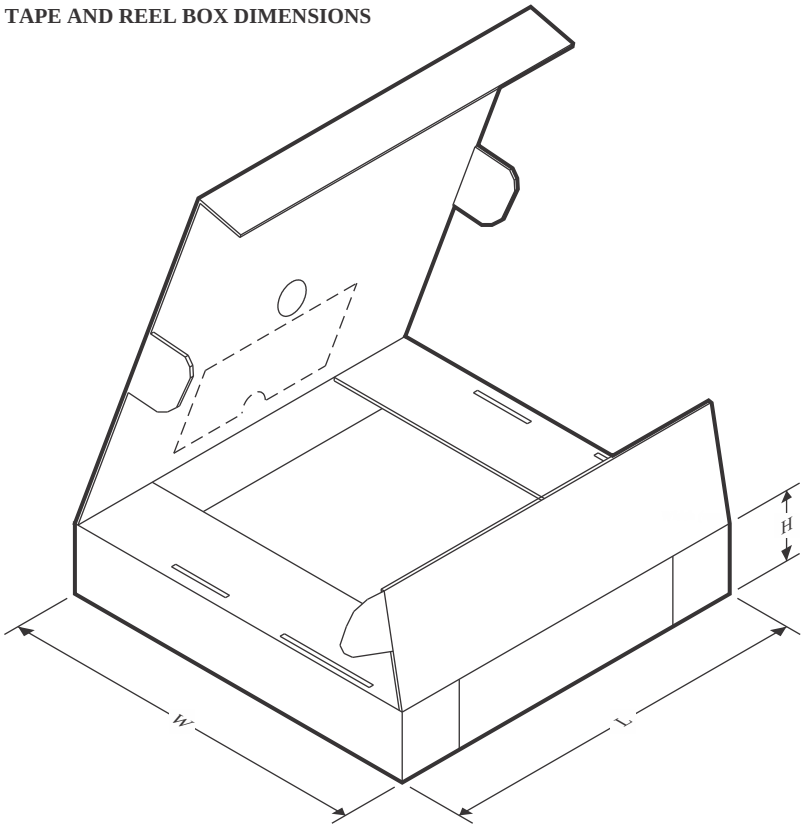
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC2G241DCTRE4	SSOP	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
74LVC2G241DCTRG4	SSOP	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
74LVC2G241DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241DCTR	SSOP	DCT	8	3000	180.0	12.4	3.15	4.35	1.55	4.0	12.0	Q3
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241DCUT	VSSOP	DCU	8	250	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241YZPR	DSBGA	YZP	8	3000	180.0	8.4	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

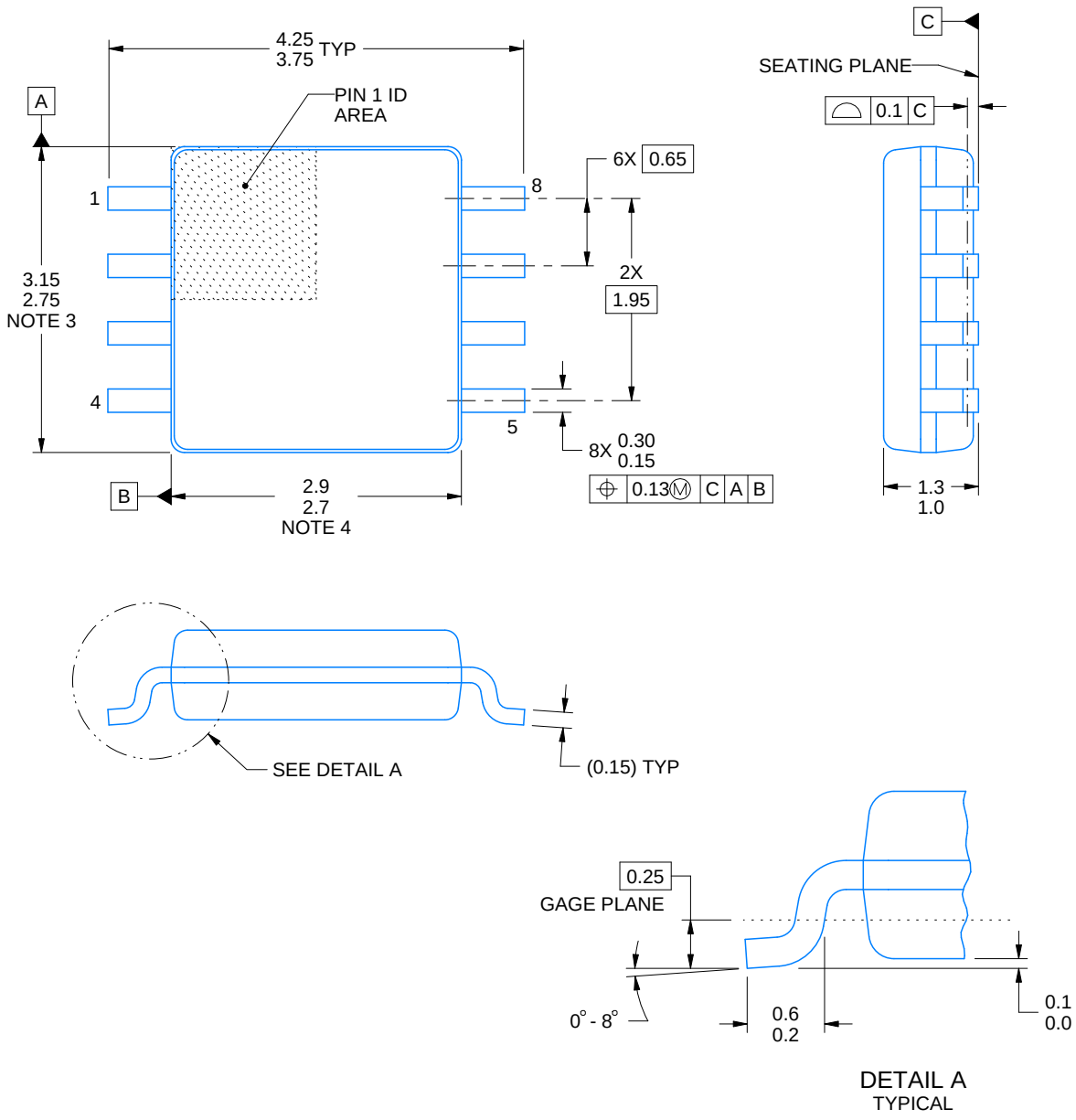
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC2G241DCTRE4	SSOP	DCT	8	3000	182.0	182.0	20.0
74LVC2G241DCTRG4	SSOP	DCT	8	3000	182.0	182.0	20.0
74LVC2G241DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G241DCTR	SSOP	DCT	8	3000	190.0	190.0	30.0
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2G241DCUT	VSSOP	DCU	8	250	180.0	180.0	18.0
SN74LVC2G241YZPR	DSBGA	YZP	8	3000	182.0	182.0	20.0

PACKAGE OUTLINE

DCT0008A

SSOP - 1.3 mm max height

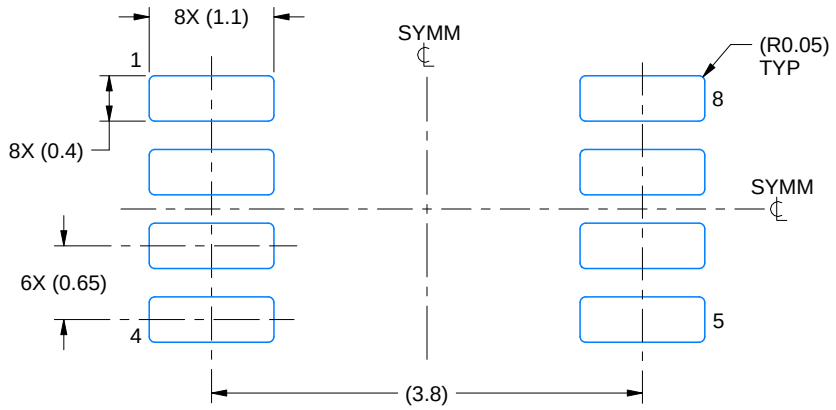
SMALL OUTLINE PACKAGE



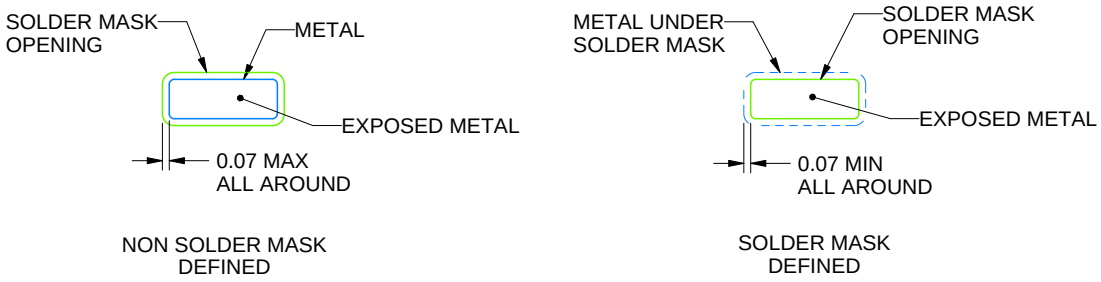
4220784/C 06/2021

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

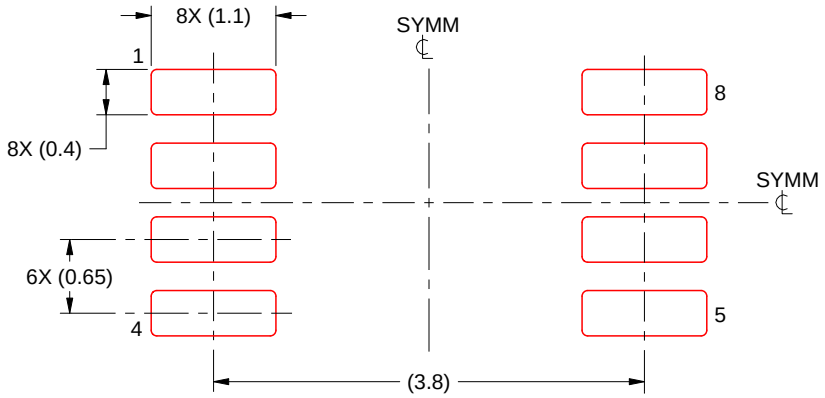


SOLDER MASK DETAILS

4220784/C 06/2021

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4220784/C 06/2021

NOTES: (continued)

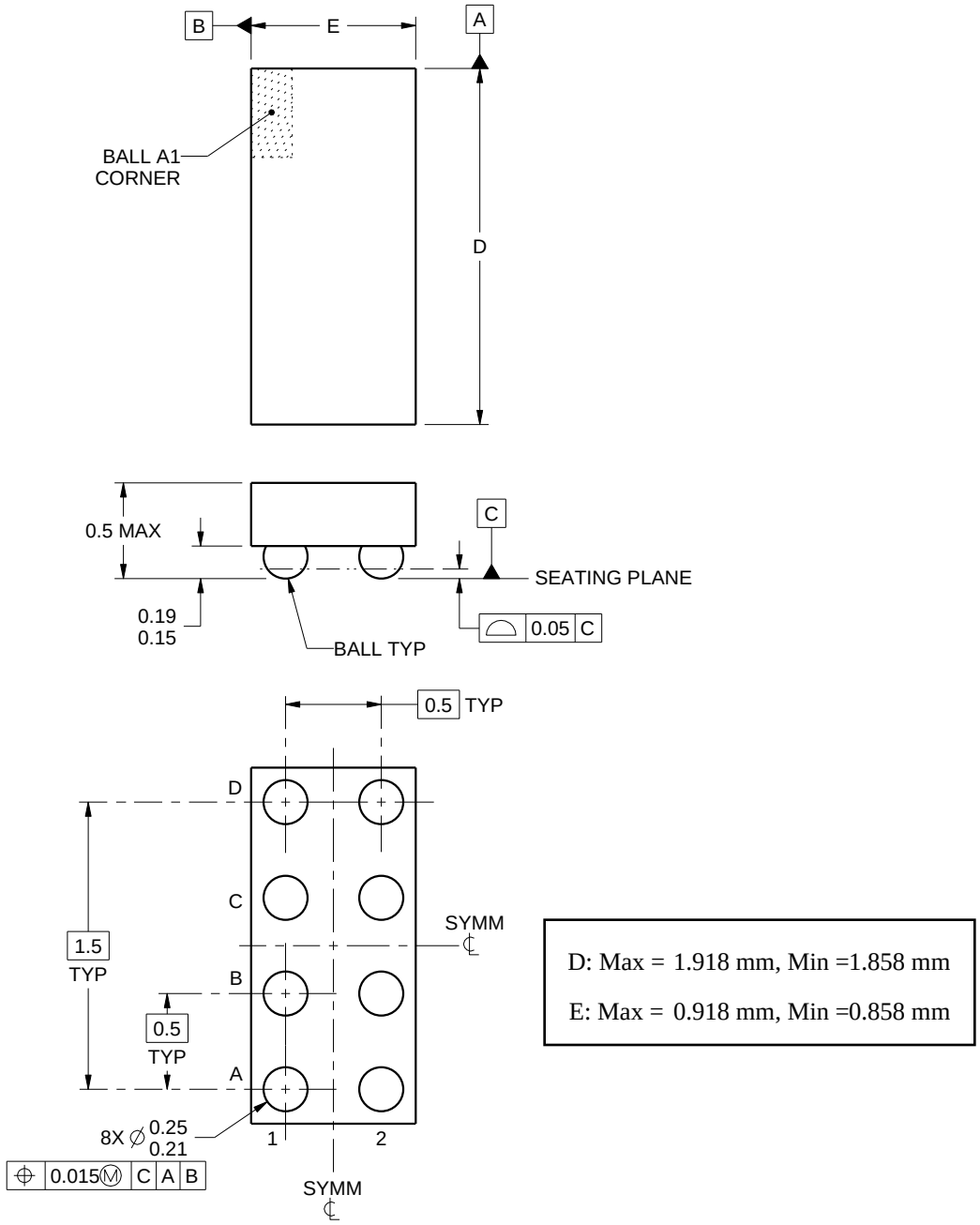
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

YZP0008

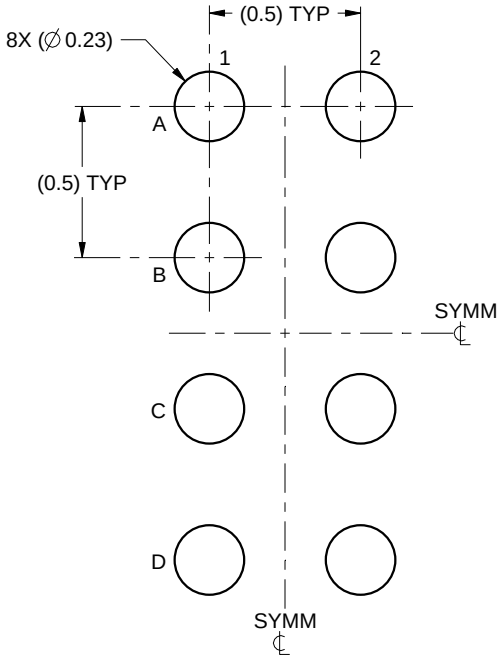
DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY

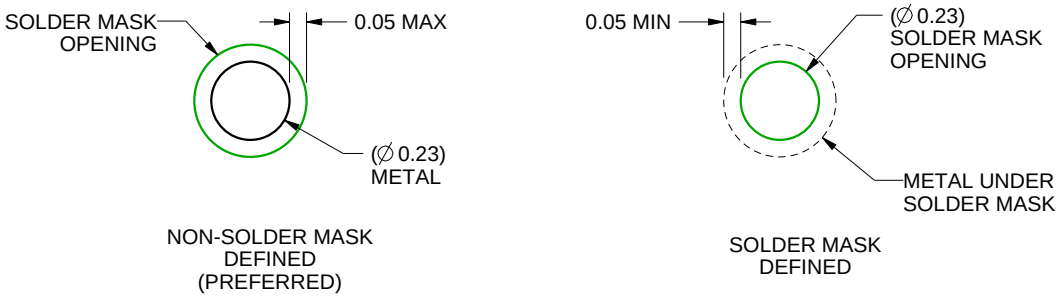


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:40X

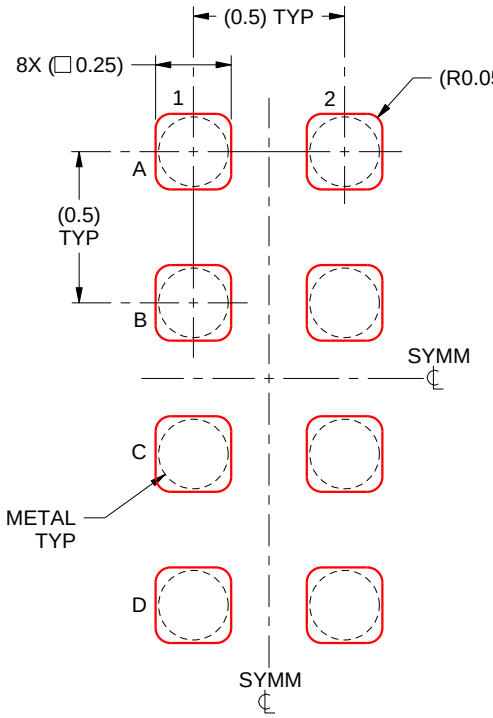


SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4223082/A 07/2016

NOTES: (continued)

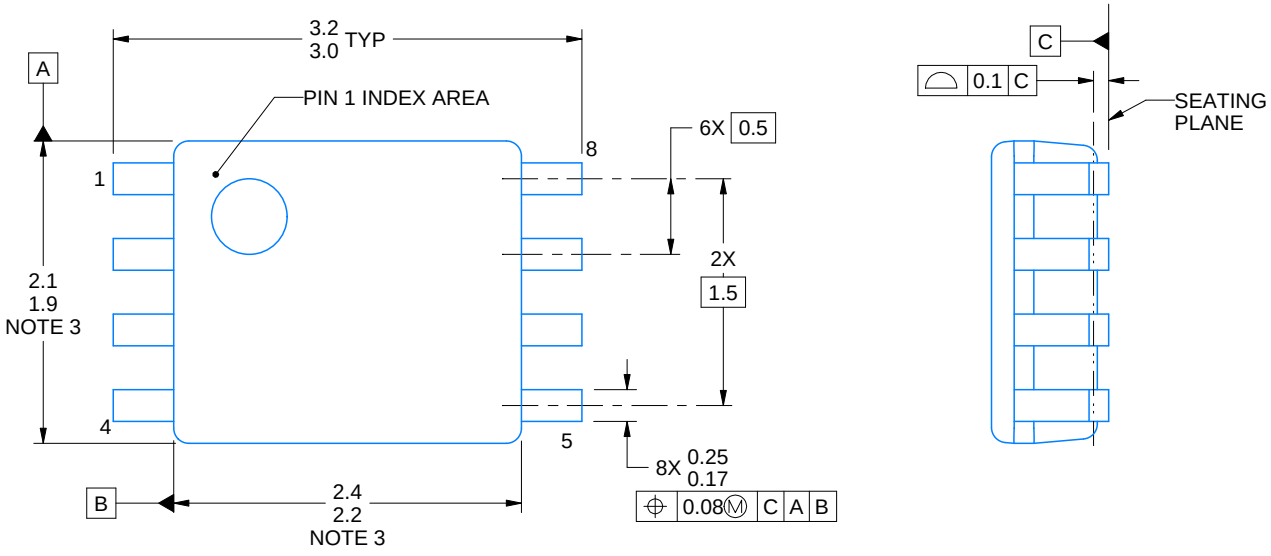
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

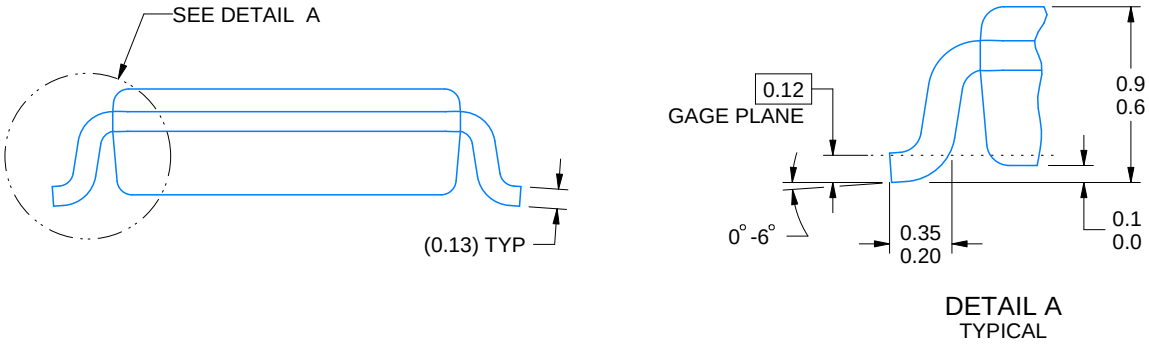
DCU0008A

PACKAGE OUTLINE

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE

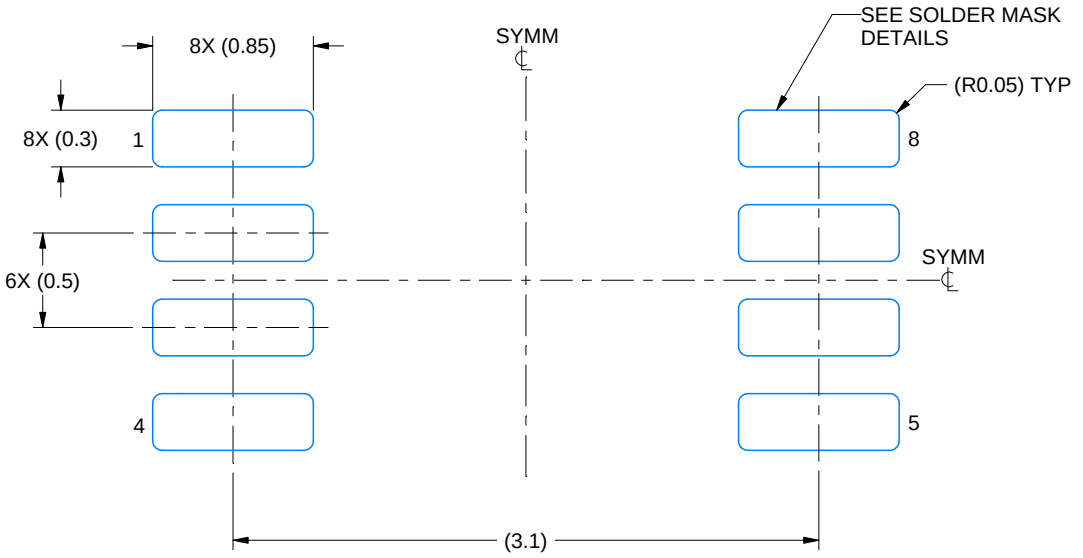




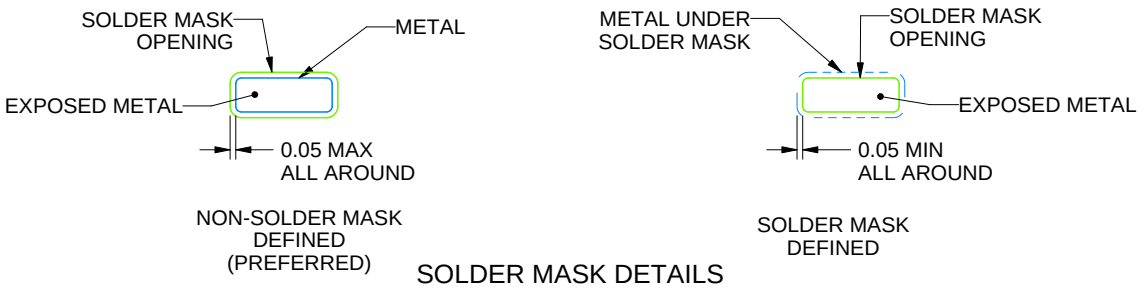
4225266/A 09/2014

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-187 variation CA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 25X

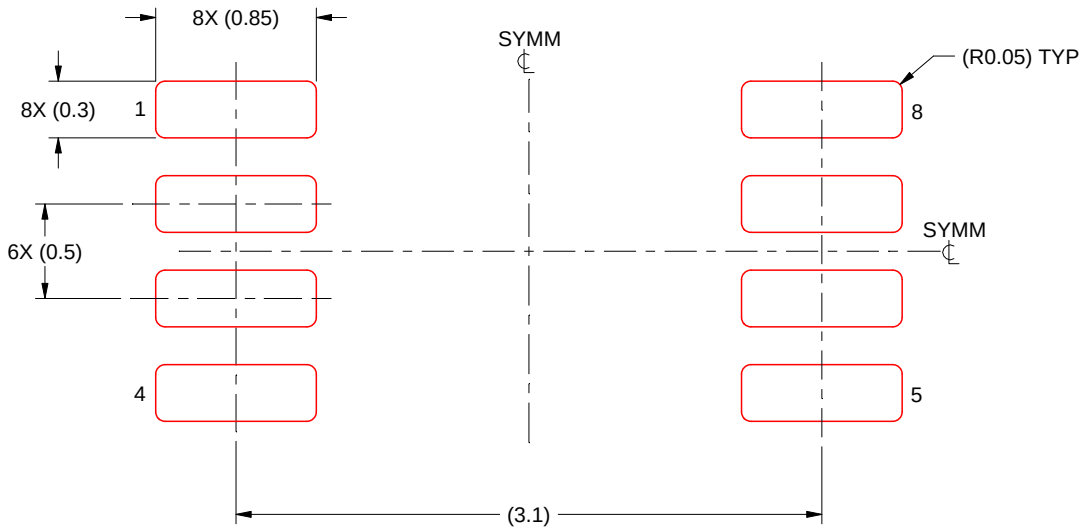


SOLDER MASK DETAILS

4225266/A 09/2014

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 25X

4225266/A 09/2014

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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